Text of the abstract

A 3D semiconductor device comprising a plurality of first transistors, overlaid by a plurality of second transistors, overlaid by a plurality of third transistors, overlaid by a plurality of fourth transistors, wherein said second transistors, said third transistors and said fourth transistors are self-aligned, having been processed following the same lithography step, and wherein at least one of said first transistors is part of a control circuit controlling at least one of said second transistors, at least one of said third transistors and at least one of said fourth transistors.